

Features

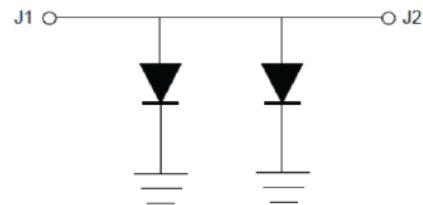
- Frequency: 0.1-40GHz
- Insertion Loss: 0.4dB typ.
- Isolation: 40dB typ.
- P-1dB: 32dBm
- Input/Output: 50Ω
- Die Size: 1.4x 0.58 x 0.1 mm

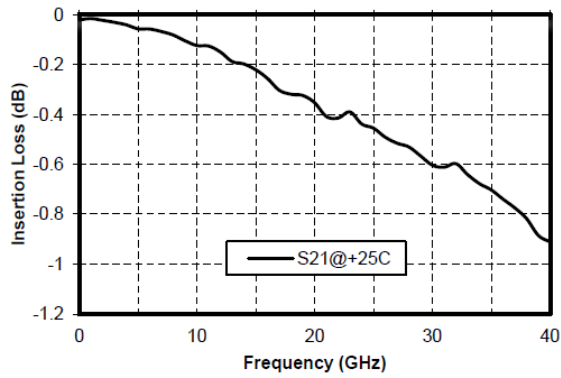
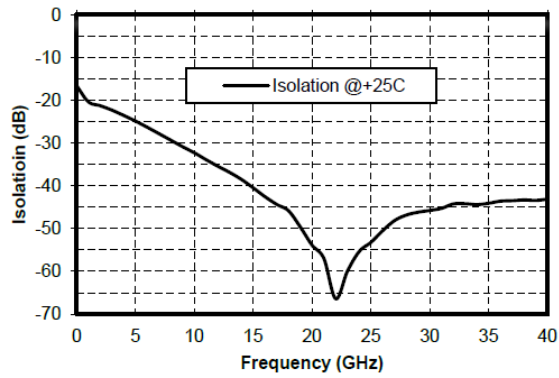
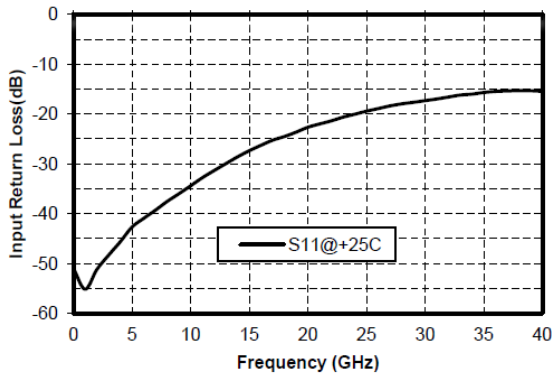
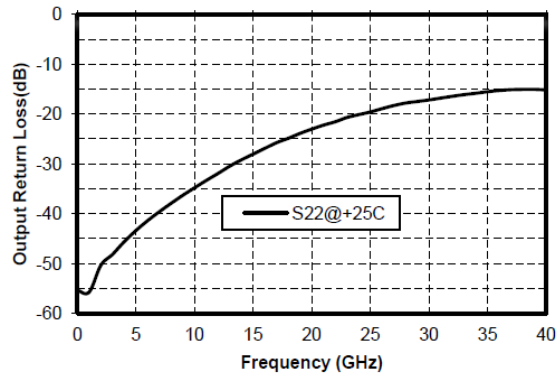
Typical Applications

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

Electrical Specifications
TA = +25°C

Parameters	Min.	Typ.	Max.	Units
Frequency Range	0.1-18			GHz
Insertion Loss	-	0.15	0.3	dB
Isolation	16	31	-	dB
Input Return Loss	24	37	-	dB
Output Return Loss	24	36	-	dB
Frequency Range	18-40			GHz
Insertion Loss	-	0.6	0.9	dB
Isolation	43	48	-	dB
Input Return Loss	15	18	-	dB
Output Return Loss	15	18	-	dB
P-1dB	-	32	-	dBm
Switching Speed	-	10	-	ns

Functional Block Diagram


Insertion Loss vs. Operating Frequency

Isolation vs. Operating Frequency

Input Return Loss vs. Operating Frequency

Output Return Loss vs. Operating Frequency

Typical Driver Connections

CONTROL LEVEL (DC CURRENT)	RF OUTPUT STATE
IN(J1) or OUT(J2)	IN(J1)-OUT(J2)
-5V	Low Loss
+10mA	Isolation



Outline Drawing

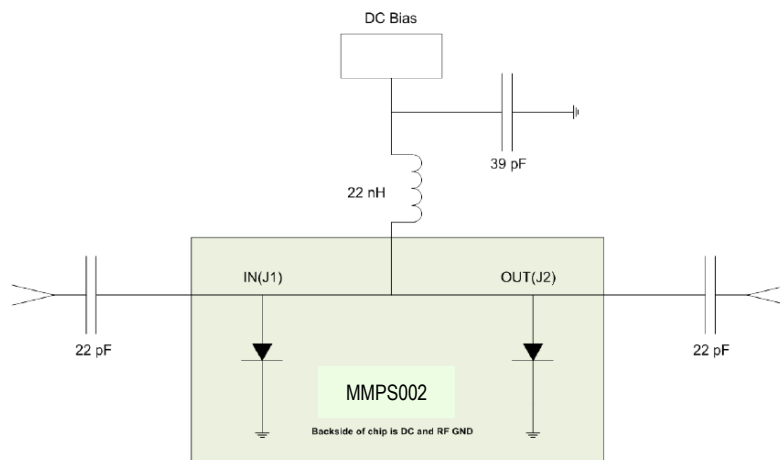
All Dimensions in μm



Pad Description

Pad	Function	Description
1	J1 (IN)	RF signal port, DC blocking capacitor needed.
2	J2 (OUT)	RF signal port, DC blocking capacitor needed.
Die bottom	GND	Die bottom must be connected to RF/DC ground.

Assembly Drawing



Notes:

1. Die thickness: 100 μm
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. Maximum input voltage: 25V
2. Maximum input power: +36dBm CW
3. Operating temperature: -55 $^{\circ}\text{C}$ to +85 $^{\circ}\text{C}$
4. Storage temperature: -65 $^{\circ}\text{C}$ to +150 $^{\circ}\text{C}$